

General Description

The MAX3355E integrates a charge pump and comparators to enable a system with an integrated USB onthe-go (OTG) dual-role transceiver to function as a USB OTG dual-role device. USB OTG facilitates the direct connection of peripherals and mobile devices such as PDAs, cellular phones, MP3 players, and digital cameras to one another without a host PC.

The MAX3355E's internal charge pump supplies V_{BUS} power and signaling that is required by the transceiver as defined in On-the-Go Supplement to the USB 2.0 Specification, Revision 1.0. The MAX3355E features ID detection and internal comparators for monitoring VBUS. The VBUS status outputs are used during negotiation for the USB according to the session request protocol (SRP) and host negotiation protocol (HNP).

The MAX3355E operates with logic supply voltages (VL) as low as 1.65V, ensuring compatibility with lowvoltage ASICs. The device also features a logic-selectable 1µA shutdown mode.

The MAX3355E has built-in ±15kV ESD-protection circuitry to protect the VBUS and ID_IN pins. The device is available in a miniature 4 x 3 chip-scale package (UCSP), as well as a 14-pin TSSOP package, and is specified for operation over the -40°C to +85°C extended temperature range.

Applications

Cell Phones MP3 Players **PDAs** Digital Cameras

Features

- ♦ Guaranteed 8mA (min) VBUS Charge-Pump Output
- ♦ ±15kV ESD Protection on V_{BUS} and ID_IN
- ♦ Up to +6.0V Backdrive Capability for V_{BUS}
- ♦ +2.6V to +5.5V Operating Voltage Range
- ♦ V_L Operates Down to +1.65V
- **♦** Guaranteed V_{BUS} Input Impedance When Not Driven
- **♦ Automatic CLOAD Detection**
- **♦** Comparators for Host Negotiation Protocol
- ♦ ID IN Detection
- ♦ Available in 4 x 3 UCSP or 14-Pin TSSOP Package

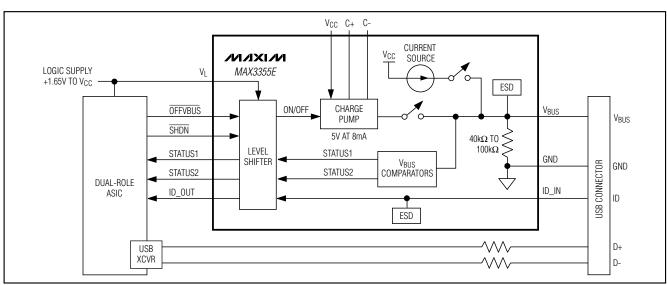
Ordering Information

PART	TEMP RANGE	PIN- PACKAGE	TOP MARK
MAX3355EEBC-T*	-40°C to +85°C	4 x 3 UCSP	ABE
MAX3355EEUD	-40°C to +85°C	14 TSSOP	_

^{*}Future product—contact factory for availability.

Pin Configurations appear at end of data sheet.

Functional Diagram



MIXIM

Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

(All voltages referenced to GND)	
VCC, VL, VBUS, ID_IN	0.3V to +6.0V
C+	(V _{CC} - 0.3V) to +6V
C	0.3V to $(V_{CC} + 0.3V)$
OFFVBUS, SHDN, STATUS1,	
STATUS2, ID_OUT	0.3V to $(V_L + 0.3V)$
VBUS Short Circuit to GND	Continuous
Output Current (all other pins)	±15mA
Continuous Power Dissipation (TA	$= +70^{\circ}C)$
4 x 3 UCSP (derate 6.5mW/°C a	bove +70°C)520mW

14-Pin TSSOP (derate 9.1mW/°C above -	+70°C)727mW
Operating Temperature Range	40°C to +85°C
Storage Temperature Range	65°C to +150°C
Junction Temperature	+150°C
Lead Temperature (soldering 10s)	+300°C
Bump Temperature (soldering)	
Infrared (15s)	+200°C
Vapor Phase (20s)	+215°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{CC} = +2.6V \text{ to } +5.5V, V_L = +1.65V \text{ to } V_{CC}, C1 = 0.1 \mu F, V_{CC}$ decoupled with $1\mu F$ capacitor to GND, V_L decoupled with $0.1 \mu F$ capacitor to GND, $C_{LOAD} = 1 \mu F$ (min), $ESR_{LOAD} = 1 \Omega$ (max), $T_A = T_{MIN}$ to T_{MAX} . Typical values are at $V_{CC} = +3.0V$, $V_L = 1.8V$, $T_A = +25^{\circ}C$, unless otherwise noted.) (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	Vcc		2.6		5.5	V
Logic Supply Voltage	VL		1.65		V _C C	V
Logic Supply Current	ΙL				100	μΑ
On availage Councils Courses	laa	No activity on V _{BUS} ; comparator and reference active			200	μΑ
Operating Supply Current	ICC	Device A configured, OFFVBUS = V _L , I _{LOAD} = 8mA, charge pump on			20	mA
Charteles and Carried a Commont	1	Device B configured, SHDN = GND			1	
Shutdown Supply Current	ICCSHDN	Device A configured, SHDN = GND		30		μA
Thermal-Shutdown Protection Threshold		Device A configured, OFFVBUS = V _L , charge pump on		+150		°C
Thermal-Shutdown Protection Hysteresis		Device A configured, OFFVBUS = V _L , charge pump on		+20		°C
LOGIC INPUTS AND OUTPUTS						
STATUS1, STATUS2, ID_OUT	VoH	ISOURCE = +1mA	2/3 x V _L			V
Output Voltage	V _{OL}	I _{SINK} = -1mA			0.4	V
OFFVBUS, SHDN Input Voltage	VIH		2/3 x V _L			V
Or vbos, sribin input voitage	VIL				0.4	V
Input Leakage Current	I _{LKG}	OFFVBUS, SHDN = GND or VL			±1	μΑ
V _{BUS} OUTPUT VOLTAGE: DEVICE	A CONFIGUR	ED				
V. Ostava Valta ara		$I_{LOAD} = 0$ to 8mA, $C_{LOAD} = 1\mu F$, $\overline{OFFVBUS} = V_L$, $ID_IN = GND$	4.63		5.25	N.
VBUS Output Voltage		No load, $C_{LOAD} = 1\mu F$, $\overline{OFFVBUS} = V_L$, $ID_IN = GND$		4.8		- V
V _{BUS} Leakage Voltage		OFFVBUS = GND			200	mV
V _{BUS} Sink Current		OFFVBUS = GND, V _{BUS} = +6.0V			150	μΑ

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC}=+2.6V\ to\ +5.5V,\ V_L=+1.65V\ to\ V_{CC},\ C1=0.1\mu F,\ V_{CC}$ decoupled with 1 μF capacitor to GND, V_L decoupled with 0.1 μF capacitor to GND, $C_{LOAD}=1\mu F$ (min), ESR $_{LOAD}=1\Omega$ (max), $T_A=T_{MIN}$ to T_{MAX} . Typical values are at $V_{CC}=+3.0V,\ V_L=1.8V,\ T_A=+25^{\circ}C$, unless otherwise noted.) (Notes 1, 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V _{BUS} Source Current		OFFVBUS = V _L , ID_IN = GND	8			mA
V _{BUS} Short-Circuit Current Limit		V _{BUS} shorted to GND			200	mA
V _{BUS} Output Ripple		$I_{LOAD} = 8mA$, $C_{LOAD} = 1\mu F$, $\overline{OFFVBUS} = V_L$, $ID_IN = GND$ (Note 3)		100		mV
Charge-Pump Switching Frequency				500		kHz
V _{BUS} Input Impedance	RINVBUS	OFFVBUS = GND or SHDN = GND	40		100	kΩ
LOAD DETECTION VBUS OUTPUT						
V _{BUS} Output Voltage		C _{LOAD} = 20µF, OFFVBUS = V _L , ID_IN = V _{CC} , I _{BUS} source on-time = t _V BUSCHRG	2.1			V
		C _{LOAD} = 95µF, OFFVBUS = V _L , ID_IN = V _{CC} , I _{BUS} source on-time = t _V BUSCHRG			1.9	
V _{BUS} Source Current		OFFVBUS = V _L , ID_IN = V _{CC} (Note 4)	450	600	850	μΑ
V _{BUS} Current Gate Time	tvbuschrg	OFFVBUS = V _L , ID_IN = V _{CC} , Device B (Note 4)	155 (max)	105	56 (min)	ms
V _{BUS} COMPARATOR						
V _{BUS} Valid Comparator Threshold	VTHVBUSVLD	V _{BUS} rising	4.4	4.55	4.63	V
V _{BUS} Valid Comparator Hysteresis				20		mV
Session Valid Comparator Threshold	V _{THSESVLD}		1.12	1.4	1.68	V
Session Valid Comparator Hysteresis				15		mV
B-Session End Comparator Threshold	VTHSESEND		0.4	0.5	0.6	V
B-Session End Comparator Hysteresis				30		mV
Shutdown Comparator	V _{TH} ,SHDN		0.8		2.4	V
ID_IN	,					
ID_IN Voltage Input for Device B			2/3 x V _{cc}			V
ID_IN Voltage Input for Device A					0.4	V
ID_IN Input Impedance			150	200	250	kΩ
ESD PROTECTION (ID_IN, VBUS)						
Human Body Model				±15		kV
IFC 1000-4-2 Air-Gap Discharge				±15		kV
IFC 1000-4-2 Contact Discharge				±8		kV



TIMING CHARACTERISTICS

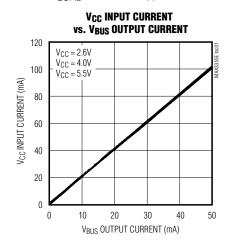
 $(V_{CC}=+2.6V\ to\ +5.5V,\ V_L=+1.65V\ to\ V_{CC},\ C1=0.1\mu F,\ V_{CC}$ decoupled with 1 μF capacitor to GND, V_L decoupled with 0.1 μF capacitor to GND, $C_{LOAD}=1\mu F$ (min), $ESR_{LOAD}=1\Omega$ (max), $T_A=T_{MIN}$ to T_{MAX} . Typical values are at $V_{CC}=+3.0V,\ V_L=1.8V,\ T_A=+25^{\circ}C$, unless otherwise noted.) (Notes 1, 2)

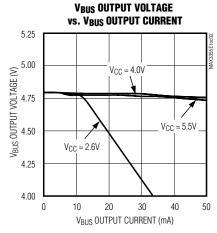
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
V _{BUS} Rise Time		0 to 4.4V, $C_{LOAD} = 1\mu F$, $I_{LOAD} = 8mA$			100	ms
OFFVBUS Propagation Delay				6		μs
Comparator Propagation Delay				3		μs
Time to Exit Shutdown				50		μs
Time to Shutdown				1		μs
ID_OUT Rise Time		C _{ID_OUT} = 50pF	·	10		ns
ID_OUT Fall Time		C _{ID_OUT} = 50pF		10		ns

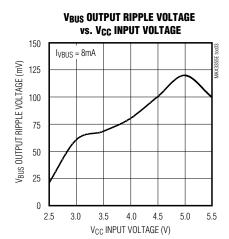
- Note 1: Limits are 100% production tested at +25°C. Limits over temperature are guaranteed by design.
- **Note 2:** All currents out of the device are positive; all currents into the device are negative. All voltages are referenced to device ground unless otherwise specified.
- Note 3: The ripple voltage is strongly correlated to the bus capacitance and its ESR.
- Note 4: The V_{BUS} current source and current gate time vary together with process and temperature such that the resulting V_{BUS} pulse is guaranteed to drive a <13µF load to a voltage >2.0V, and to drive a >96µF load to a voltage <2.2V.

Typical Operating Characteristics

(V_{CC}, V_L = +3.3V, C1 = 0.1 μ F, V_{CC} decoupled with 1 μ F capacitor to GND, V_L decoupled with 0.1 μ F capacitor to GND, C_{LOAD} = 1 μ F min, ESR_{LOAD} = 1 Ω max, T_A = +25°C, unless otherwise noted.)

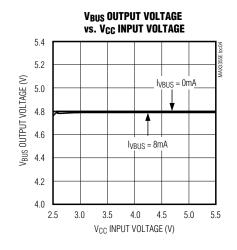


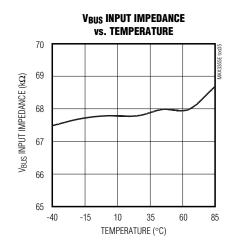


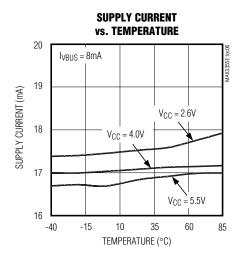


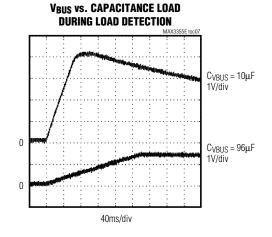
Typical Operating Characteristics (continued)

 $(V_{CC}, V_L = +3.3V, C1 = 0.1 \mu F, V_{CC}$ decoupled with 1 μF capacitor to GND, V_L decoupled with 0.1 μF capacitor to GND, $C_{LOAD} = 1 \mu F$ min, $ESR_{LOAD} = 1\Omega$ max, $T_A = +25^{\circ}C$, unless otherwise noted.)





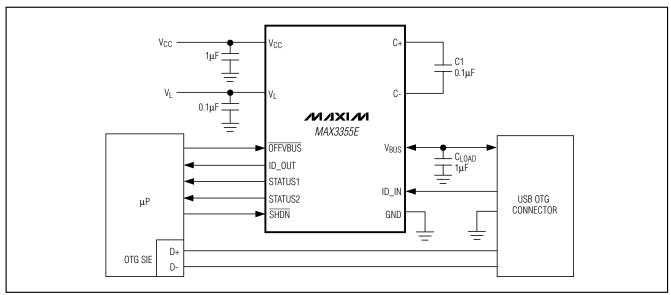




Pin Description

PIN NAME		NAME	FUNCTION
UCSP	TSSOP	INAME	FUNCTION
A1	2	Vcc	Power Supply. +2.6V to +5.5V input supply. Bypass V _{CC} to GND with a 1µF capacitor.
A2	3	ID_OUT	Device ID Output. Output of ID_IN level translated to V _L .
А3	5	STATUS1	Status Output 1. Provides output voltage detection for use during HNP handshaking (Tables 1 and 2).
A4	6	STATUS2	Status Output 2. Provides output voltage detection for use during HNP handshaking (Tables 1 and 2).
B1	1	V _{BUS}	USB Supply. V _{BUS} provides a nominal +5.0V output when ID_IN is low and OFFVBUS is high. V _{BUS} is lower than +2.1V when ID_IN is open or a load greater than 96.5µF is sensed. V _{BUS} can be backdriven to +6.0V without any consequence. Bypass V _{BUS} to GND with a 1µF capacitor.
B2	4	<u>OFFVBUS</u>	V _{BUS} Off. Turns the internal charge pump providing V _{BUS} on and off.
ВЗ	11	SHDN	Shutdown. Connect \overline{SHDN} to GND to enter shutdown and reduce supply current to less than 1 μ A. Connect \overline{SHDN} to V _L for normal operation.
B4	9	VL	Logic Supply. V_L sets the logic output high voltage and logic input high threshold. V_L must be between +1.65V and V_{CC} .
C1	14	C+	Charge-Pump Positive Connection
C2	13	C-	Charge-Pump Negative Connection
СЗ	12	GND	Ground
C4	10	ID_IN	Device ID. ID_IN is internally pulled up to V _{CC} . Leave ID_IN open for device B and connect ID_IN to GND for device A.
	7, 8	N.C.	No Connection

Typical Application Circuit



Detailed Description

USB OTG is an emerging USB standard that enables devices to talk in a peer-to-peer manner on a USB bus. OTG allows peripherals and mobile devices such as PDAs, cellular phones, and digital cameras to be attached directly to one another without requiring a PC host.

The MAX3355E integrates a charge pump and comparators to enable a system with an integrated USB OTG dual-role transceiver to function as a USB OTG dual-role device. The MAX3355E's internal charge pump supplies VBUS power and signaling as defined in *On-the-Go Supplement: USB 2.0, Revision 1.0.* The MAX3355E's internal level-detection comparators monitor important VBUS voltages needed to support SRP and HNP.

Table 1. Status Bit Significance

STATUS1	STATUS2	SIGNIFICANCE
0	0	V _{BUS} < V _{THSESEND}
1	0	VTHSESEND < VBUS < VTHSESVLD
0	1	VTHSESVLD < VBUS < VTHVBUSVLD
1	1	V _{BUS} > V _{THV} BUSVLD

Table 2. Status Bit Shutdown Functionality (SHDN = GND)

STATUS1	STATUS2	SIGNIFICANCE
0	1	V _{BUS} < V _{TH} , SHDN
0	0	V _{BUS} > V _{TH} , SHDN

Table 3. Device ID

ID_IN	ID_OUT	CONFIGURATION
0	0	Device A
Open	VL	Device B

Charge Pump

The MAX3355E provides power for the V_{BUS} line using an internal charge pump. The charge pump provides an OTG-compliant output on V_{BUS} while sourcing 8mA load current. The charge pump can be powered from voltages between +2.6V and +5.5V. A 0.1 μ F flying capacitor, connected between C+ and C-, and a 1 μ F (min) decoupling reservoir capacitor on V_{BUS} are required for proper operation.

The charge pump is active if $\overline{\text{OFFVBUS}}$ is connected to V_L and the MAX3355E is configured as device A (ID_IN connected to GND). To minimize V_{BUS} ripple, select a reservoir capacitor value between 1µF and 6.8µF. The charge-pump output is protected from short-circuit conditions on V_{BUS} by an internal current clamp that limits the V_{BUS} current to 200mA.

Current Generator

An internal current generator injects up to $600\mu A$ of current onto the V_{BUS} line. The current generator is stable over the supply voltage variation. The current generator is connected to V_{BUS} when $\overline{\text{OFFVBUS}}$ and $\overline{\text{SHDN}}$ are 1 and ID_IN is open. It remains connected for ty_{BUSCHRG} or until the V_{BUS} line voltage exceeds the lower of V_{CC} and 4.82V.

Comparators

The MAX3355E contains internal comparators for monitoring the VBUS voltage. The status of VBUS is summarized in two status outputs: STATUS1 and STATUS2. The status outputs can be used to negotiate for the USB OTG bus. The VBUS status is conveyed according to Table 1. While in shutdown mode, the STATUS2 output can be used to indicate VBUS voltage (Table 2).

Device ID

Configure the MAX3355E as device A by connecting ID_IN to GND and as device B by leaving ID_IN open (Table 3). ID_IN is level translated to V_L and provided as an output at ID_OUT. V_L sets the logic output high level. ID_IN is internally pulled up to V_CC.

Table 4. Function Select

SHDN	OFFVBUS	ID_IN	V _{BUS}	CHARGE PUMP	COMPARATORS
0	X	X	RINVBUS	Inactive	Inactive
1	0	X	RINVBUS	Inactive	Active
1	1	0	5V	Active	Active
1	1	1	R _{INVBUS} (Note 5)	Inactive	Active

Note: The 600µA current source is supplied for tyBUSCHRG (see the Current Generator section).

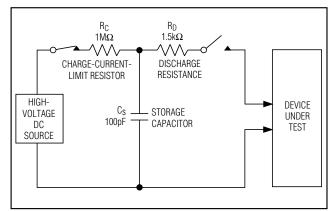


Figure 1. Human Body ESD Test Model

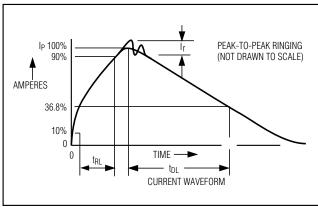


Figure 2. Human Body Current Waveform

OFFVBUS

Connect $\overline{\text{OFFVBUS}}$ to GND to disable V_{BUS} and the charge pump (Table 4). For normal V_{BUS} operation, connect $\overline{\text{OFFVBUS}}$ to V_L. When $\overline{\text{OFFVBUS}}$ = GND, V_{BUS} impedance is between 40k Ω to 100k Ω as defined in *Onthe-Go Supplement: USB 2.0, Revision 1.0.*

SHDN

The MAX3355E shutdown mode reduces supply current to less than 1 μ A. To enter shutdown mode, connect SHDN to GND. Shutdown mode disables the charge pump and comparators (Table 4). While in shutdown mode, the STATUS1 output defaults to logic 0 and STATUS2 indicates VBUS. During shutdown, if VBUS is externally driven above VTH, SHDN (defined in the *Comparators* section), the MAX3355E sinks current from VCC.

Applications Information_ ±15kV ESD Protection

To protect the MAX3355E against ESD, ID_IN and VBUS

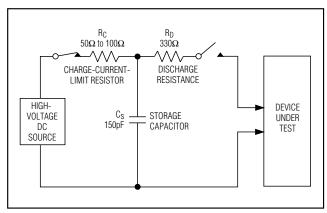


Figure 3. IEC 1000-4-2 ESD Test Model

have extra protection against static electricity to protect the device up to $\pm 15 \text{kV}$. For $\pm 15 \text{kV}$ protection on V_{BUS}, a 1µF capacitor must be connected from V_{BUS} to GND as close to the device as possible. The ESD structures withstand high ESD in all states—normal operation, shutdown, and powered down. ESD protection can be tested in various ways. The ID_IN input and V_{BUS} are characterized for protection to the following limits:

- 1) ±15kV using the Human Body Model
- ±8kV using the IEC 1000-4-2 Contact Discharge method
- 3) ±15kV using the IEC 1000-4-2 Air-Gap Discharge method

ESD performance depends on a variety of conditions. Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

Human Body Model

Figure 1 shows the Human Body Model and Figure 2 shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the test device through a $1.5 \mathrm{k}\Omega$ resistor.

IEC 1000-4-2

The IEC 1000-4-2 standard covers ESD testing and performance of finished equipment. It does not specifically refer to integrated circuits. The MAX3355E helps the user design equipment that meets Level 4 of IEC 1000-4-2, without the need for additional ESD-protection components. The major difference between tests done using the Human Body Model and IEC 1000-4-2 is a higher peak current in IEC 1000-4-2. This occurs because series resistance is lower in the IEC 1000-4-2 model. Hence, the ESD withstand voltage measured to

IEC 1000-4-2 is generally lower than that measured using the Human Body Model. Figure 3 shows the IEC 1000-4-2 model. The Air-Gap Discharge test involves approaching the device with a charged probe. The contact-discharge method connects the probe to the device before the probe is energized.

Machine Model

The Machine Model for ESD tests all pins using a 200pF storage capacitor and zero discharge resistance. Its objective is to emulate the stress caused by contact that occurs with handling and assembly during manufacturing. All pins require this protection during manufacturing. After PC board assembly, the Machine Model is less relevant to I/O ports.

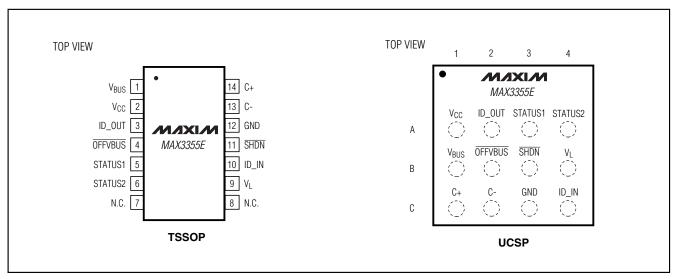
Layout Considerations

The MAX3355E charge-pump switching frequency makes proper layout important to ensure stability and maintain the output voltage under all loads. For best performance, minimize the distance between the capacitors and the MAX3355E.

UCSP Applications Information

For the latest application details on UCSP construction, dimensions, tape-carrier information, printed circuit board techniques, bump-pad layout, and recommended reflow temperature profile, as well as the latest information on reliability testing results, refer to Maxim Application Note: *UCSP-A Wafer-Level Chip-Scale Package* available on Maxim's web site at www.maxim-ic.com/ucsp.

Pin Configurations



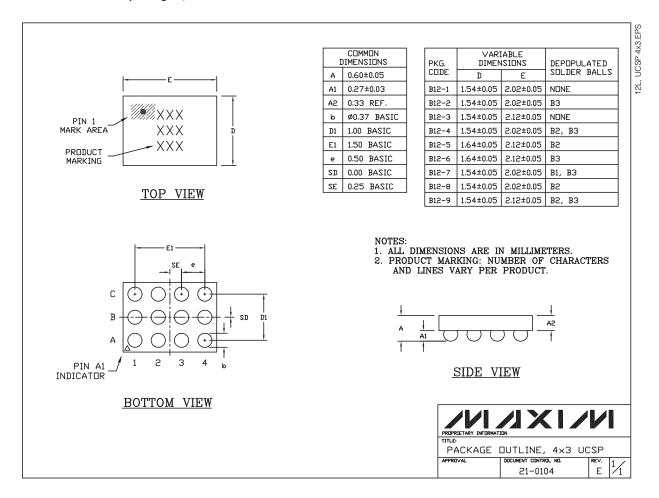
Chip Information

TRANSISTOR COUNT: 1601

PROCESS: BICMOS

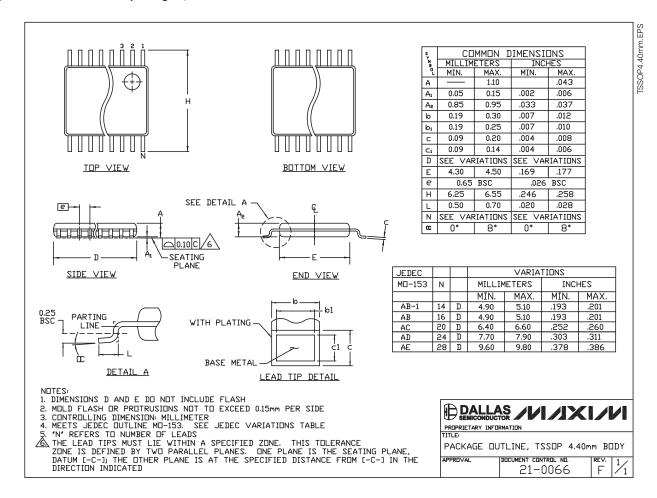
Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-ic.com/packages.)



Package Information (continued)

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